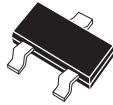


**CMPT3640**  
**PNP SILICON TRANSISTOR**



**SOT-23 CASE**

# Central<sup>TM</sup>

**Semiconductor Corp.**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMPT3640 type is a PNP silicon transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for saturated switching applications.

**MARKING CODE: C2J**

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

	SYMBOL		UNITS
Collector-Base Voltage	$V_{CBO}$	12	V
Collector-Emitter Voltage	$V_{CEO}$	12	V
Emitter-Base Voltage	$V_{EBO}$	4.0	V
Continuous Collector Current	$I_C$	80	mA
Power Dissipation	$P_D$	350	mW
Operating and Storage			
Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
Thermal Resistance	$\Theta_{JA}$	357	$^\circ\text{C/W}$

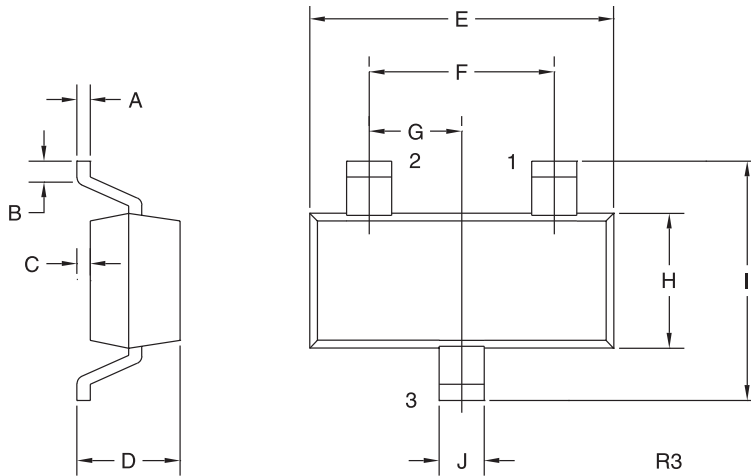
**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$I_{CES}$	$V_{CE}=6.0\text{V}$		10	nA
$I_{CES}$	$V_{CE}=6.0\text{V}, T_A=65^\circ\text{C}$		10	$\mu\text{A}$
$I_B$	$V_{CE}=6.0\text{V}, V_{EB}=0$		10	nA
$BV_{CBO}$	$I_C=100\mu\text{A}$	12		V
$BV_{CEO}$	$I_C=10\text{mA}$	12		V
$BV_{EBO}$	$I_E=100\mu\text{A}$	4.0		V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		0.20	V
$V_{CE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$		0.60	V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}, T_A=65^\circ\text{C}$		0.25	V
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=0.5\text{mA}$	0.75	0.95	V
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$	0.80	1.00	V
$V_{BE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$		1.50	V
$h_{FE}$	$V_{CE}=0.3\text{V}, I_C=10\text{mA}$	30	120	
$h_{FE}$	$V_{CE}=1.0\text{V}, I_C=50\text{mA}$	20		
$f_T$	$V_{CE}=5.0\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	500		MHz
$C_{ob}$	$V_{CB}=5.0\text{V}, I_E=0, f=1.0\text{MHz}$		3.5	pF
$C_{ib}$	$V_{BE}=0.5\text{V}, I_C=0, f=1.0\text{MHz}$		3.5	pF
$t_d$	$V_{CC}=6.0\text{V}, V_{BE}=1.9, I_C=50\text{mA}, I_{B1}=5.0\text{mA}$		10	ns
$t_r$	$V_{CC}=6.0\text{V}, V_{BE}=1.9, I_C=50\text{mA}, I_{B1}=5.0\text{mA}$		30	ns

**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$t_s$	$V_{CC}=6.0\text{V}$ , $I_C=50\text{mA}$ , $I_{B1}=I_{B2}=5.0\text{mA}$		20	ns
$t_f$	$V_{CC}=6.0\text{V}$ , $I_C=50\text{mA}$ , $I_{B1}=I_{B2}=5.0\text{mA}$		12	ns
$t_{on}$	$V_{CC}=6.0\text{V}$ , $V_{BE}=1.9$ , $I_C=50\text{mA}$ , $I_{B1}=5.0\text{mA}$		25	ns
$t_{on}$	$V_{CC}=1.5\text{V}$ , $I_C=10\text{mA}$ , $I_{B1}=0.5\text{mA}$		60	ns
$t_{off}$	$V_{CC}=6.0\text{V}$ , $V_{BE}=1.9$ , $I_C=50\text{mA}$ , $I_{B1}=5.0\text{mA}$		35	ns
$t_{off}$	$V_{CC}=1.5\text{V}$ , $I_C=10\text{mA}$ , $I_{B1}=I_{B2}=0.5\text{mA}$		75	ns

**SOT-23 CASE - MECHANICAL OUTLINE**



**LEAD CODE:**

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR

**MARKING CODE: C2J**

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)